Amplifier Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
	5088 5089	30 25	Vdc
	5088 5089	35 30	Vdc
Emitter – Base Voltage	V _{EBO}	3.0	Vdc
Collector Current – Continuous	Ic	50	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	C P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W

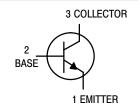
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

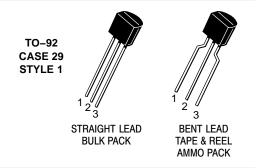
1. $R_{\theta JA}$ is measured with the device soldered into a typical printed circuit board.



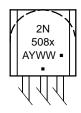
ON Semiconductor®

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MARKING DIAGRAM



x = 8 or 9

A = Assembly Location

Y = Year

WW = Work Week

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
2N5088G	TO-92 (Pb-Free)	5000 Units/Bulk
2N2088RLRAG	TO-92 (Pb-Free)	2000/Tape & Reel
2N5089G	TO-92 (Pb-Free)	5000 Units/Bulk
2N2089RLRE	TO-92	2000/Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

$\textbf{ELECTRICAL CHARACTERISTICS} \; (T_A = 25^{\circ}C \; unless \; otherwise \; noted)$

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 2) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	2N5088 2N5089	V _{(BR)CEO}	30 25	- -	Vdc
Collector – Base Breakdown Voltage ($I_C = 100 \mu Adc, I_E = 0$)	2N5088 2N5089	V _{(BR)CBO}	35 30	- -	Vdc
Collector Cutoff Current $(V_{CB} = 20 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 15 \text{ Vdc}, I_E = 0)$	2N5088 2N5089	I _{CBO}	- -	50 50	nAdc
Emitter Cutoff Current		I _{EBO}	- -	50 100	nAdc
ON CHARACTERISTICS			•	•	
DC Current Gain ($I_C = 100 \mu Adc$, $V_{CE} = 5.0 Vdc$)	2N5088 2N5089	h _{FE}	300 400	900 1200	-
$(I_C = 1.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	2N5088 2N5089		350 450	- -	
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}) \text{ (Note 2)}$	2N5088 2N5089		300 400	- -	
Collector – Emitter Saturation Voltage (I _C = 10 mAdc, I _B = 1.0 mAdc)		V _{CE(sat)}	-	0.5	Vdc
Base – Emitter On Voltage (I _C = 10 mAdc, V _{CE} = 5.0 Vdc) (Note 2)		V _{BE(on)}	-	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product ($I_C = 500 \mu Adc$, $V_{CE} = 5.0 Vdc$, $f = 20 MHz$)		f _T	50	_	MHz
Collector–Base Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)		C _{cb}	-	4.0	pF
Emitter-Base Capacitance (V _{EB} = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{eb}	-	10	pF
Small–Signal Current Gain (I _C = 1.0 mAdc, V _{CE} = 5.0 Vdc, f = 1.0 kHz)	2N5088 2N5089	h _{fe}	350 450	1400 1800	-
Noise Figure (I _C = 100 μ Adc, V _{CE} = 5.0 Vdc, R _S = 1.0 k Ω , f = 1.0 kHz)	2N5088 2N5089	NF	- -	3.0 2.0	dB

^{2.} Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

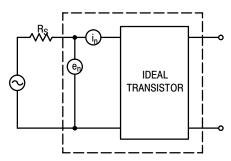
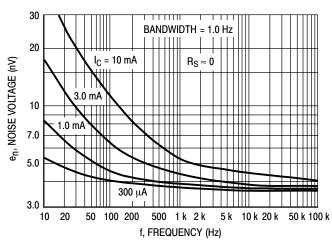


Figure 1. Transistor Noise Model

NOISE CHARACTERISTICS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$

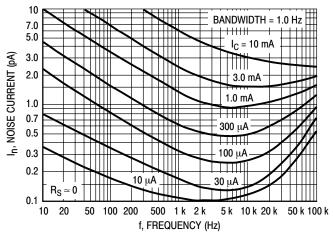
NOISE VOLTAGE



BANDWIDTH = 1.0 Hz 20 en, NOISE VOLTAGE (nV) $R_S \approx 0$ f = 10 Hz 10 100 Hz 7.0 5.0 3.0 0.01 0.02 0.1 0.2 0.5 2.0 5.0 0.05 1.0 10 IC, COLLECTOR CURRENT (mA)

Figure 2. Effects of Frequency

Figure 3. Effects of Collector Current



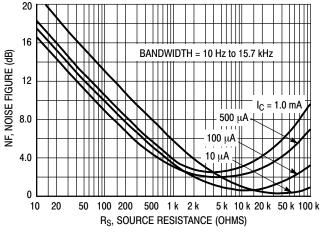
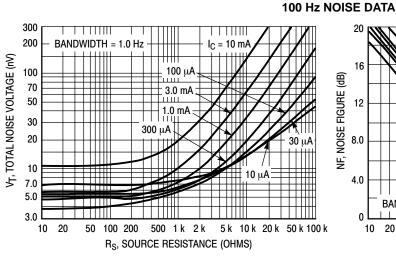


Figure 4. Noise Current

Figure 5. Wideband Noise Figure





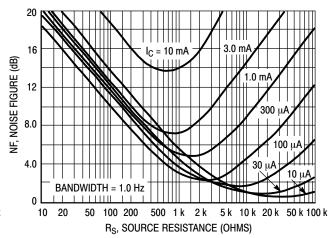


Figure 7. Noise Figure

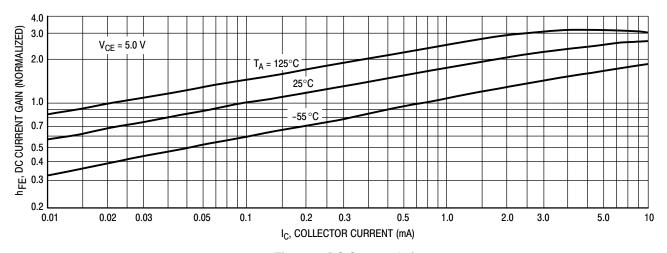


Figure 8. DC Current Gain

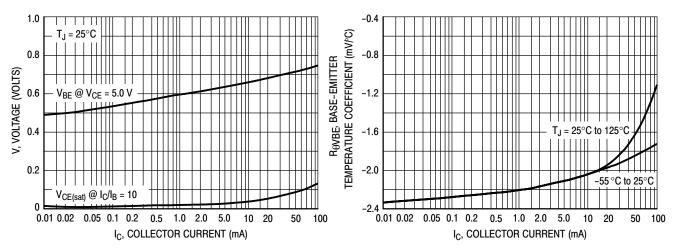


Figure 9. "On" Voltages

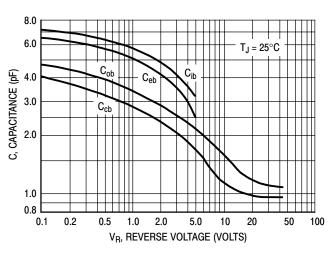


Figure 11. Capacitance

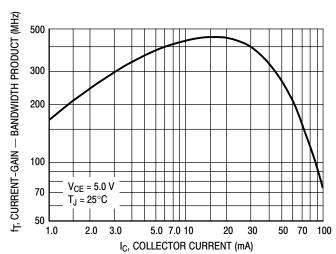
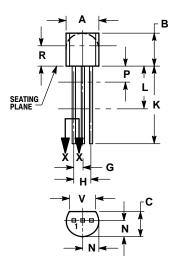


Figure 10. Temperature Coefficients

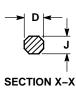
Figure 12. Current-Gain — Bandwidth Product

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**

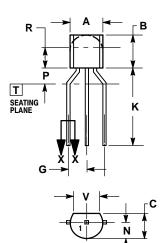


STRAIGHT LEAD **BULK PACK**



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R
- IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIM	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	



BENT LEAD TAPE & REEL AMMO PACK



NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

- ASME Y14-3M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
 DIMENSION R IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P
 AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93	-	
٧	3.43		

STYLE 1: PIN 1. EMITTER

BASE

COLLECTOR

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